

DF452

FAST RECOVERY DIODE

APPLICATIONS

- Induction Heating.
- A.C. Motor Drives.
- Inverters And Choppers.
- Welding.
- High Frequency Rectification.
- UPS.

KEY PARAMETERS

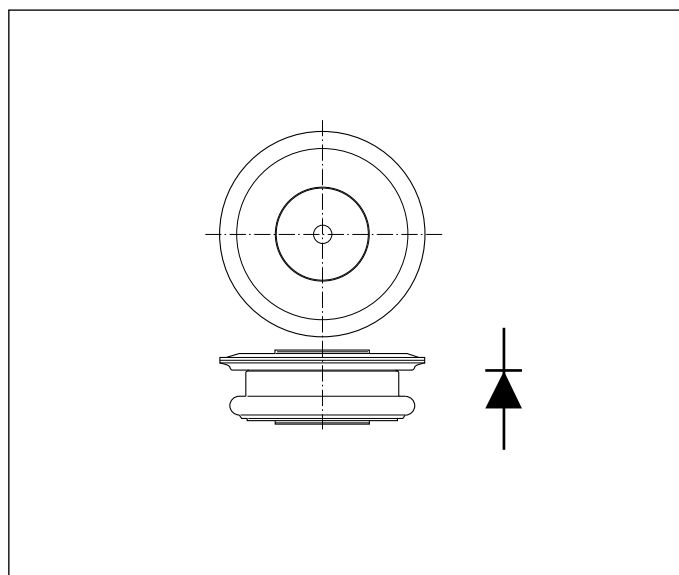
V_{RRM}	1600V
$I_{F(AV)}$	540A
I_{FSM}	5000A
Q_r	35 μ C
t_{rr}	3.2 μ s

FEATURES

- Double side cooling.
- High surge capability.
- Low recovery charge.

VOLTAGE RATINGS

Type Number	Repetitive Peak Reverse Voltage V_{RRM} V	Conditions
DF452 16	1600	$V_{RSM} = V_{RRM} + 100V$
DF452 14	1400	
DF452 12	1200	
DF452 10	1000	
DF452 08	800	
DF452 06	600	



Outline type code: M771.
See package outlines for further information.

CURRENT RATINGS

Symbol	Parameter	Conditions	Max.	Units
Double Side Cooled				
$I_{F(AV)}$	Mean forward current	Half wave resistive load, $T_{case} = 65^{\circ}C$	540	A
$I_{F(RMS)}$	RMS value	$T_{case} = 65^{\circ}C$	628	A
I_F	Continuous (direct) forward current	$T_{case} = 65^{\circ}C$	-	A
Single Side Cooled (Anode side)				
$I_{F(AV)}$	Mean forward current	Half wave resistive load, $T_{case} = 65^{\circ}C$	-	A
$I_{F(RMS)}$	RMS value	$T_{case} = 65^{\circ}C$	-	A
I_F	Continuous (direct) forward current	$T_{case} = 65^{\circ}C$	-	A

SURGE RATINGS

Symbol	Parameter	Conditions	Max.	Units
I_{FSM}	Surge (non-repetitive) forward current	10ms half sine; with 0% V_{RRM} , $T_j = 150^\circ\text{C}$	5.0	kA
I^2t	I^2t for fusing		125×10^3	A^2s
I_{FSM}	Surge (non-repetitive) forward current	10ms half sine; with 50% V_{RRM} , $T_j = 150^\circ\text{C}$	-	kA
I^2t	I^2t for fusing		-	A^2s

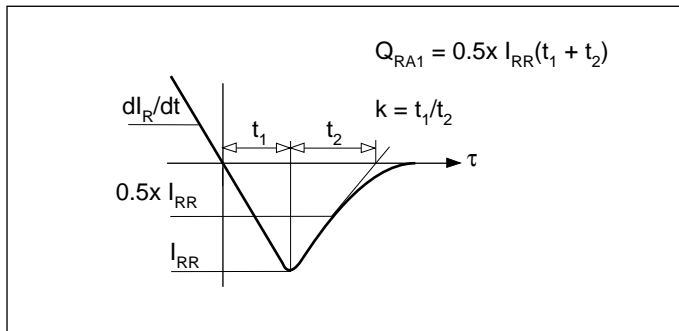
THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions		Min.	Max.	Units
$R_{th(j-c)}$	Thermal resistance - junction to case	Double side cooled	dc	-	0.07	$^\circ\text{C/W}$
		Single side cooled	Anode dc	-	0.133	$^\circ\text{C/W}$
			Cathode dc	-	0.147	$^\circ\text{C/W}$
$R_{th(c-h)}$	Thermal resistance - case to heatsink	Clamping force 5.0kN with mounting compound	Double side	-	0.02	$^\circ\text{C/W}$
			Single side	-	0.04	$^\circ\text{C/W}$
T_{vj}	Virtual junction temperature	Forward (conducting)		-	150	$^\circ\text{C}$
T_{stg}	Storage temperature range			-55	150	$^\circ\text{C}$
-	Clamping force			4.5	5.5	kN

CHARACTERISTICS

Symbol	Parameter	Conditions	Typ.	Max.	Units
V_{FM}	Forward voltage	At 750A peak, $T_{case} = 25^{\circ}C$	-	1.6	V
I_{RRM}	Peak reverse current	At V_{RRM} , $T_{case} = 150^{\circ}C$	-	40	mA
t_{rr}	Reverse recovery time	$I_F = 200A$, $di_{RR}/dt = 20A/\mu s$ $T_{case} = 125^{\circ}C$, $V_R = 100V$	3.2	-	μs
Q_{RA1}	Recovered charge (50% chord)		-	35	μC
I_{RM}	Reverse recovery current		-	43	A
K	Soft factor		1.8	-	-
V_{TO}	Threshold voltage	At $T_{vj} = 150^{\circ}C$	-	1.0	V
r_T	Slope resistance	At $T_{vj} = 150^{\circ}C$	-	0.8	$m\Omega$
V_{FRM}	Forward recovery voltage	$di/dt = 1000A/\mu s$, $T_j = 125^{\circ}C$	-	-	V

DEFINITION OF K FACTOR AND Q_{RA1}



CURVES

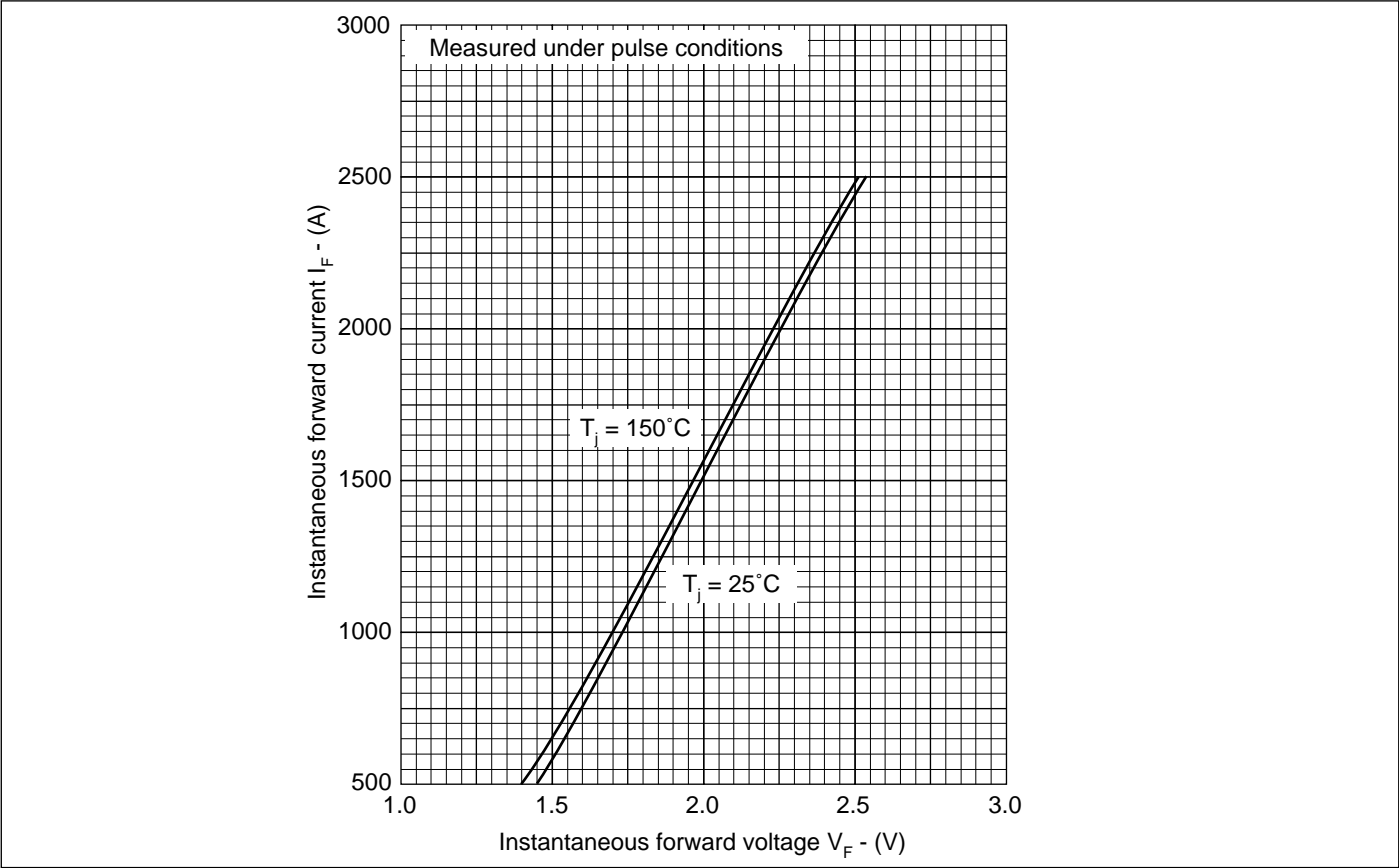


Fig.1 Maximum (limit) forward characteristics

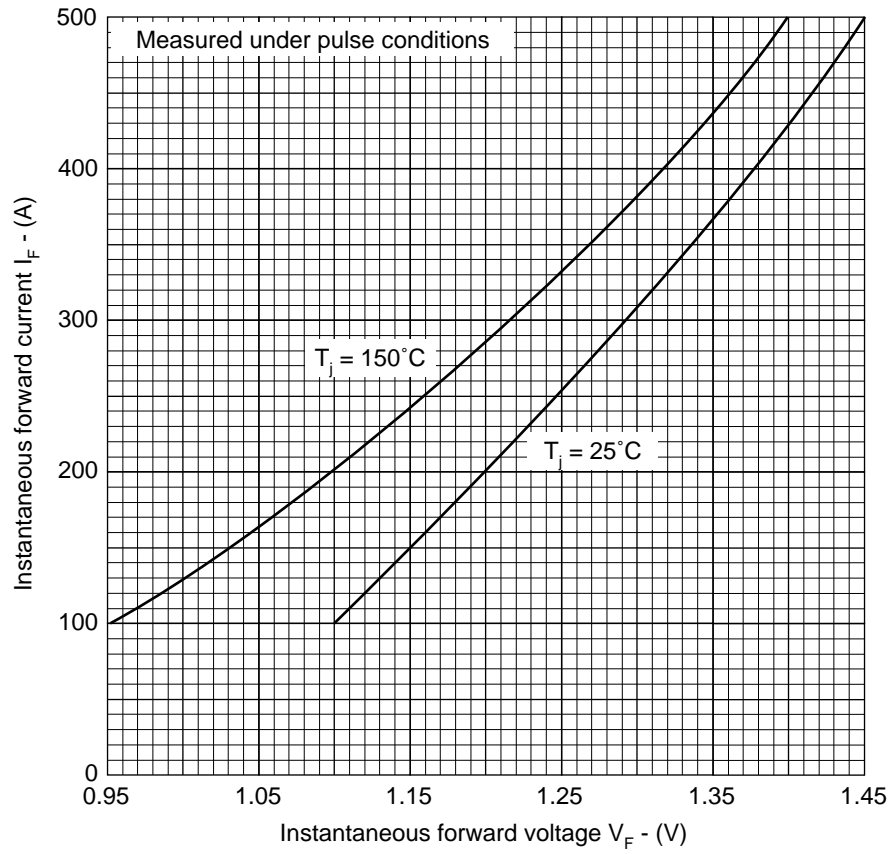


Fig.2 Maximum (limit) forward characteristics

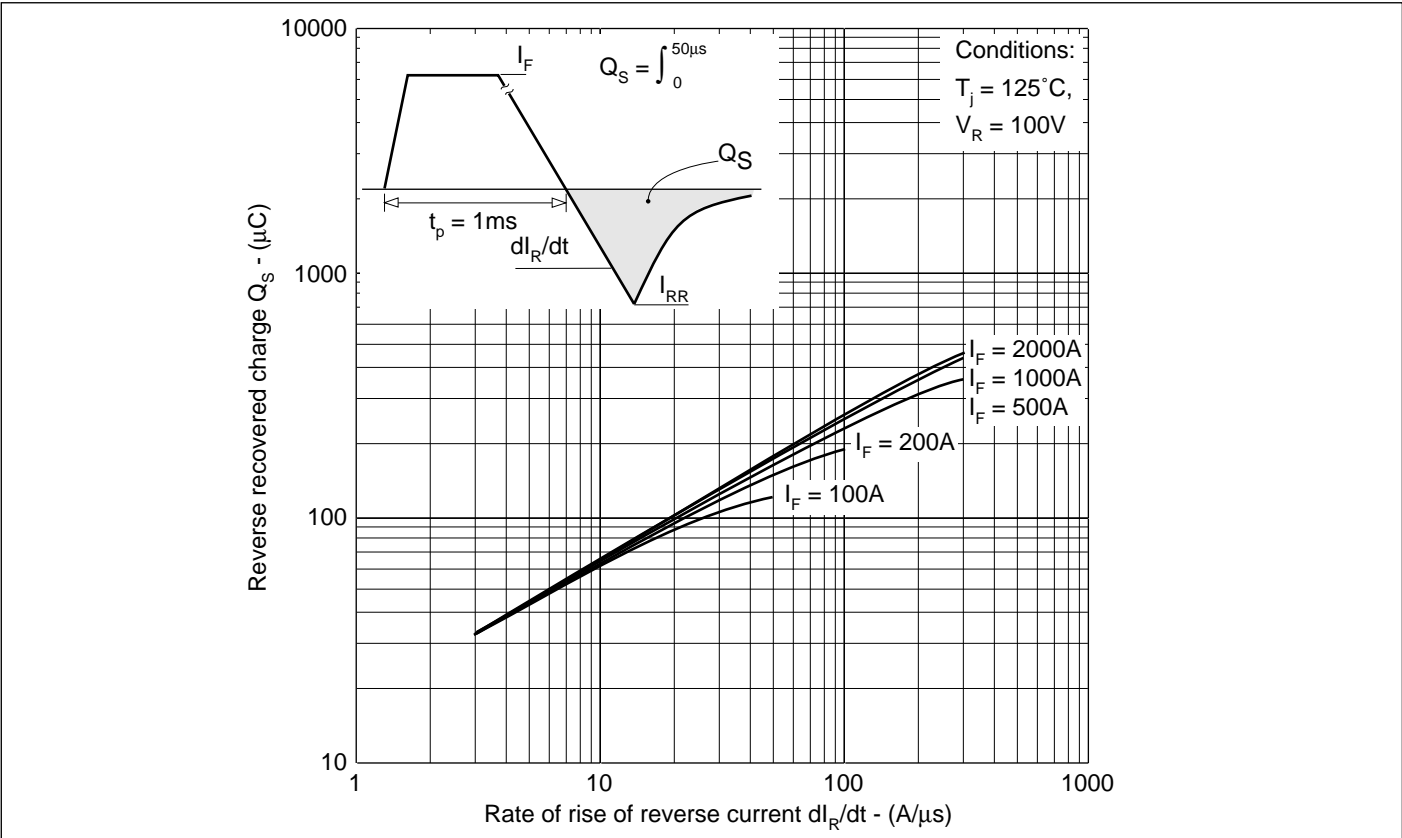


Fig.4 Recovered charge

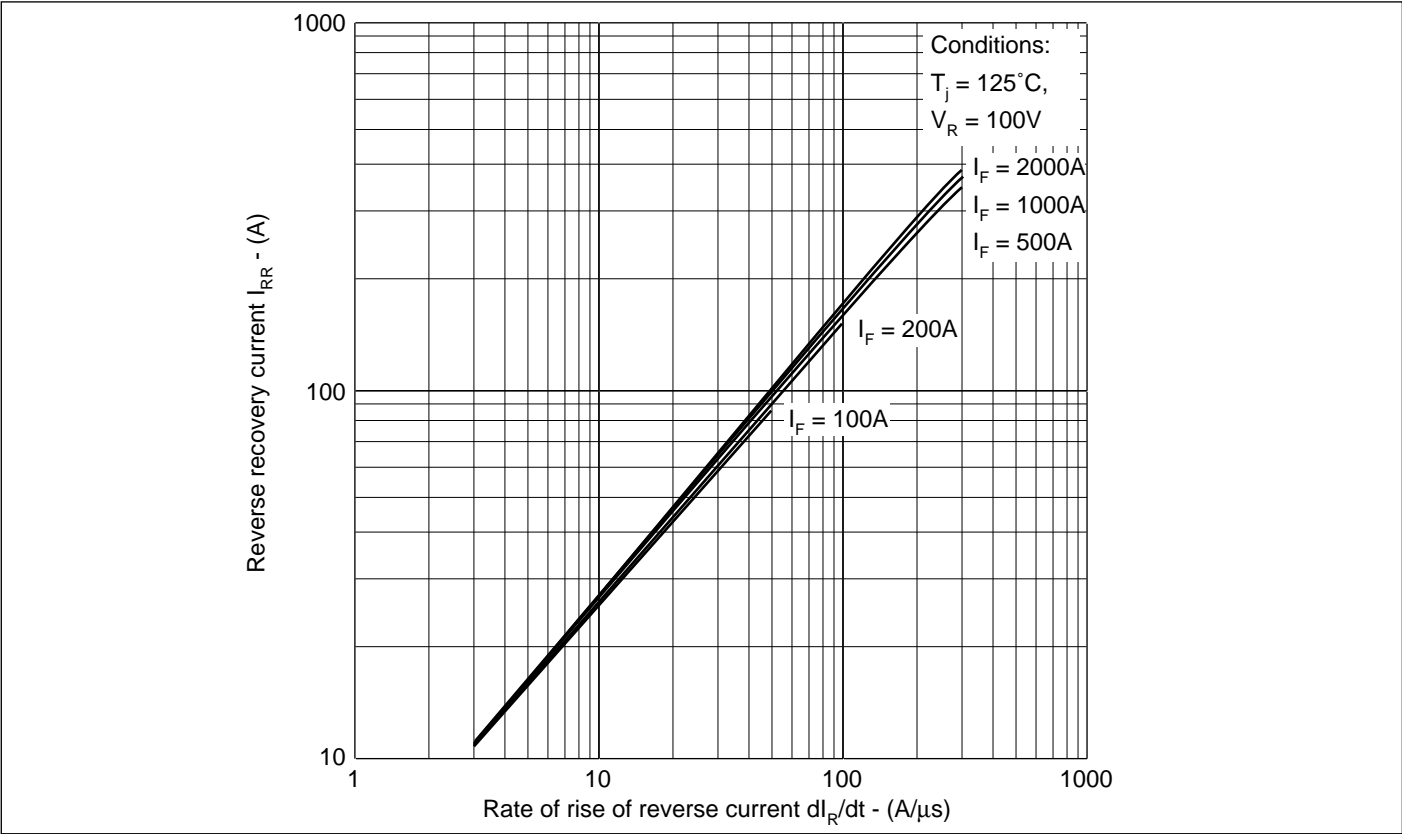


Fig.5 Typical reverse recovery current vs rate of fall of forward current

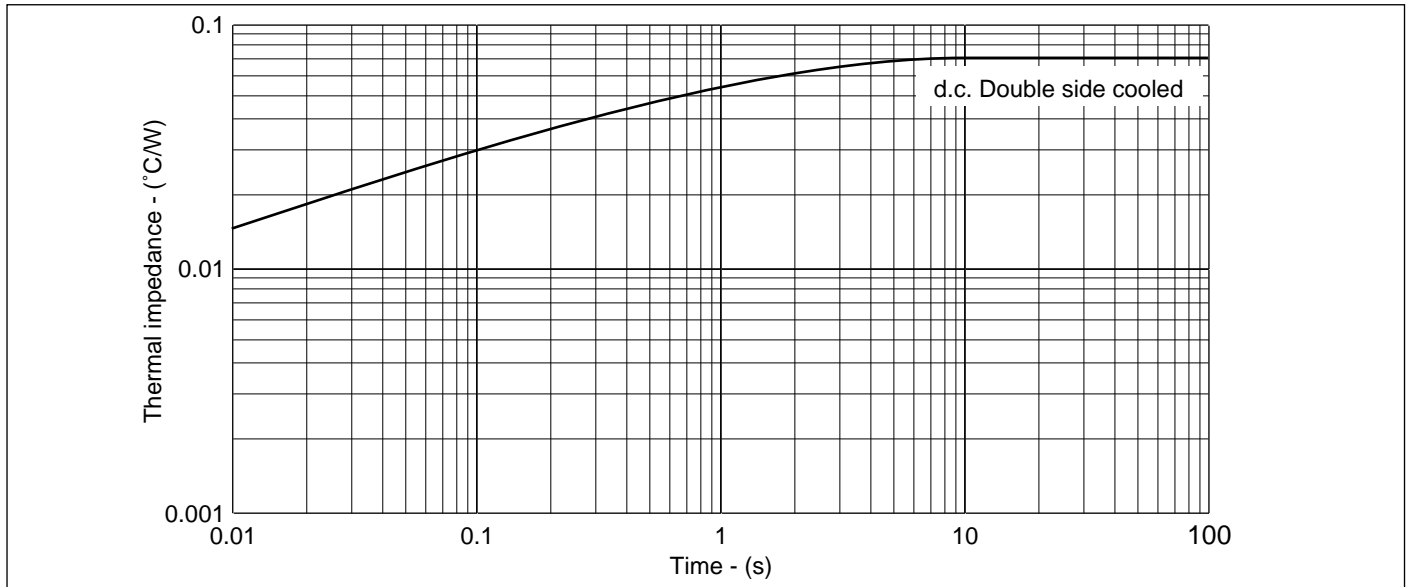
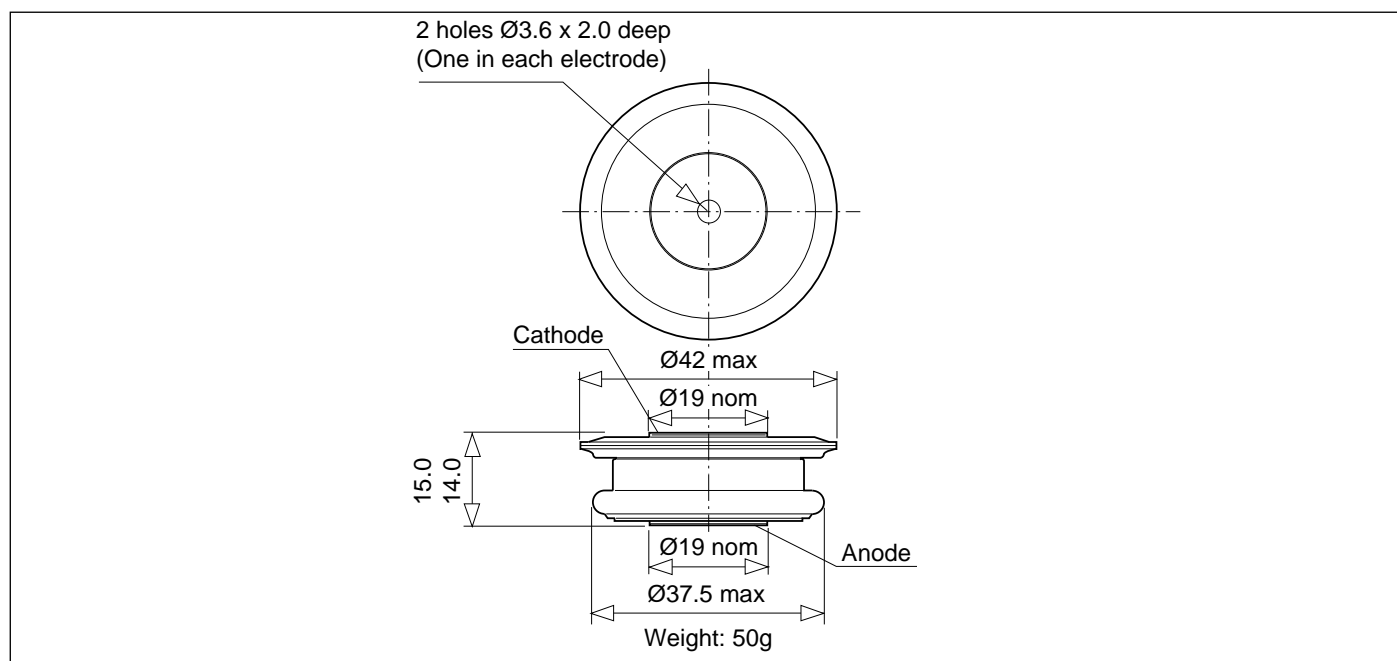


Fig.6 Maximum (limit) transient thermal impedance - junction to case - ($^{\circ}\text{C/W}$)

PACKAGE DETAILS - M771

For further package information, please contact your local Customer Service Centre. All dimensions in mm, unless stated otherwise.
DO NOT SCALE.



GEC PLESSEY
SEMICONDUCTORS

HEADQUARTERS OPERATIONS**GEC PLESSEY SEMICONDUCTORS**

Cheney Manor, Swindon,
Wiltshire, SN2 2QW, United Kingdom.

Tel: + 44 (0)1793 518000

Fax: + 44 (0)1793 518411

GEC PLESSEY SEMICONDUCTORS

P.O. Box 660017

1500 Green Hills Road,
Scotts Valley, California 95067-0017,
United States of America.

Tel: + 1 (408) 438 2900

Fax: + 1 (408) 438 5576

POWER PRODUCT CUSTOMER SERVICE CENTRES

- **FRANCE.** 2 rue Henri-Bergson, 92665 Asnieres Cedex.
Tel: + 33 1 40 80 54 00. Fax: + 33 1 40 80 55 87.
- **GERMANY.** Ungererstrasse 129, 80505 München.
Tel: + 49 (0)89 36 09 060. Fax: + 49 (0)89 36 09 06 55.
- **NORTH AMERICA.** At Dedham Place, Suite 125, 3 Allied Drive, Dedham. MA 02026.
Tel: + 1 617 251 0126. Fax: + 1 617 251 0106.
- **UNITED KINGDOM.** Doddington Road, Lincoln. LN6 3LF.
Tel: + 44 (0)1522 500500. Fax: + 44 (0)1522 500550.

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